## 2 A, 20 V Schottky Barrier **Diode**

These Schottky barrier diodes are optimized for low forward voltage drop and low leakage current and are offered in a Chip Scale Package (CSP) to reduce board space. The low thermal resistance enables designers to meet the challenging task of achieving higher efficiency and meeting reduced space requirements.

- Low Forward Voltage Drop -450 mV (Typ.) @  $I_F = 2 \text{ A}$
- Low Reverse Current  $40 \mu A$  (Typ.) @  $V_R = 20 V$
- 2 A of Continuous Forward Current
- ESD Rating Human Body Model: Class 3B
  - Machine Model: Class C
- High Switching Speed
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost dc-dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	20	V
Forward Current (DC)	lF	2	Α
Forward Surge Current (60 Hz @ 1 cycle)	I <sub>FSM</sub>	19	А
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)	I <sub>FRM</sub>	3.6	А
ESD Rating: Human Body Model Machine Model	ESD	> 8 > 400	kV V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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DSN<sub>2</sub> (0603)CASE 152AT



PIN 1 6EM

6E = Specific Device Code M = Date Code

#### **PIN CONNECTIONS**



#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NSR20206NXT5G	DSN2 (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Thermal Resistance Junction–to–Ambient (Note 1) Total Power Dissipation @ T <sub>A</sub> = 25°C	$egin{array}{c} R_{ hetaJA} \ P_D \end{array}$			245 510	°C/W mW
Thermal Resistance Junction–to–Ambient (Note 2) Total Power Dissipation @ T <sub>A</sub> = 25°C	R <sub>θJA</sub> P <sub>D</sub>			90 1.4	°C/W W
Storage Temperature Range	T <sub>stg</sub>			-40 to +125	°C
Junction Temperature	TJ			+150	°C

- 1. Mounted onto a 4 in square FR-4 board 50 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.
- 2. Mounted onto a 4 in square FR-4 board 650 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.

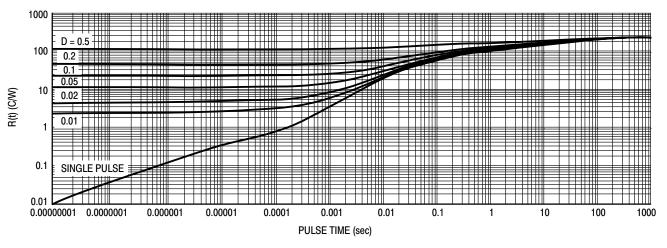


Figure 1. Thermal Response (Note 1)

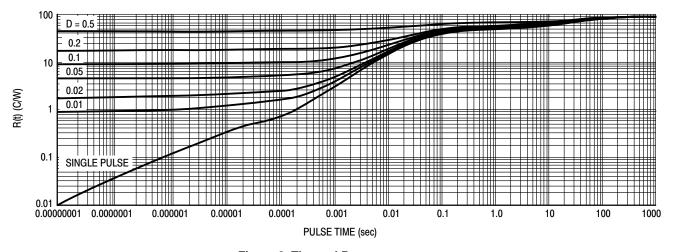
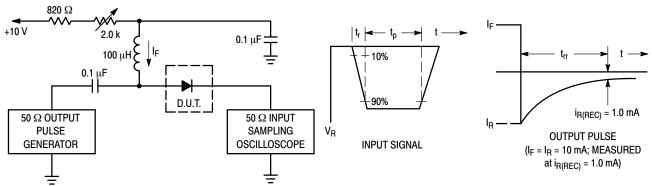


Figure 2. Thermal Response (Note 2)

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Leakage (V <sub>R</sub> = 10 V) (V <sub>R</sub> = 20 V)	I <sub>R</sub>	_ _	10 40	30 150	μΑ
Forward Voltage (I <sub>F</sub> = 10 mA) (I <sub>F</sub> = 100 mA) (I <sub>F</sub> = 500 mA) (I <sub>F</sub> = 1 A) (I <sub>F</sub> = 2 A)	V <sub>F</sub>	- - - - -	250 310 360 390 450	290 350 400 430 490	mV
Total Capacitance (V <sub>R</sub> = 2.0 V, f = 1.0 MHz)	C <sub>T</sub>	-	140	_	pF
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mA}$ , $I_{R(REC)} = 1.0 \text{ mA}$ , Figure 3)	t <sub>rr</sub>	-	75	-	ns
Peak Forward Recovery Voltage (I <sub>F</sub> = 100 mA, t <sub>r</sub> = 20 ns, Figure 4)	$V_{FRM}$	-	430	-	mV

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA.

2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.

3. t<sub>p</sub> » t<sub>rr</sub>

Figure 3. Recovery Time Equivalent Test Circuit

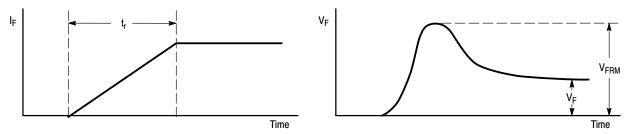
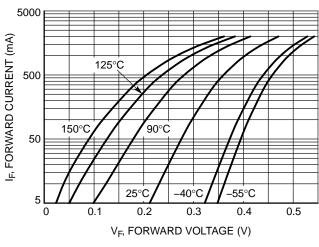


Figure 4. Peak Forward Recover Voltage Definition

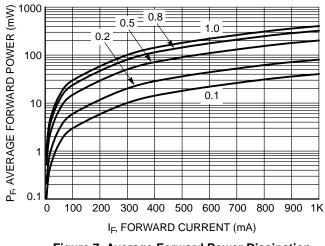
#### TYPICAL CHARACTERISTICS



10K 125°C 90°C 90°C 25°C 25°C 0.0001 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 V<sub>R</sub>, REVERSE VOLTAGE (V)

Figure 5. Forward Voltage

Figure 6. Leakage Current



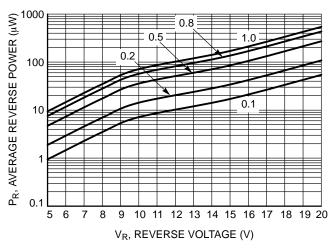
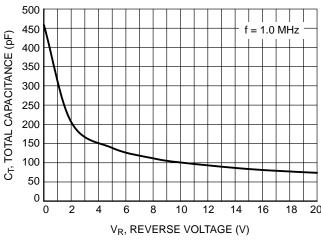


Figure 7. Average Forward Power Dissipation

Figure 8. Average Reverse Power Dissipation



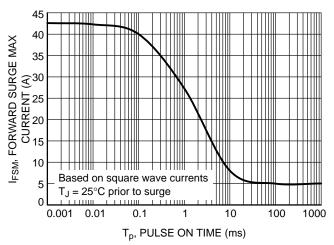
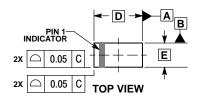


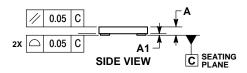
Figure 9. Total Capacitance

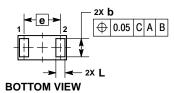
Figure 10. Forward Surge Maximum

#### PACKAGE DIMENSIONS

DSN2, 1.6x0.8, 1.2P, (0603) CASE 152AT ISSUE A





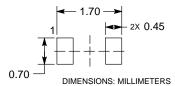


#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.25	0.31	
A1	0.00	0.05	
b	0.55	0.65	
D	1.60 BSC		
Е	0.80 BSC		
е	1.20 BSC		
Ĺ	0.25	0.35	

# RECOMMENDED MOUNTING FOOTPRINT\*



See Application Note AND8464/D for more mounting details

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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